drawn 50nm diameter = actual 50nm diameter at 360uC/cm²
drawn 80nm diameter = actual 80nm diameter at 360uC/cm²
drawn 100nm diameter = actual 100nm diameter at 250uC/cm²
100nm CAD drawn diameter, dose = 250uC/cm2
80nm CAD drawn diameter, dose = 400uC/cm²
50nm CAD drawn diameter, dose = 400uC/cm²
Process Conditions

**Substrate:** Silicon

**Resist:** ZEP520A (positive tone)
spincoat: puddle dispense, 4000RPM, 2000RPM/s, 60sec
post apply hot bake: 180C, 2min
resist thickness: 348nm

**EBL:**
acc voltage: 100kV
beam current: 2nA
shot pitch: 5nm
height setting: SFOCUS only, sample in 3D, probably -20um out of focus
pattern: 50, 80, 100nm diameter circles on 2um pitch, covering a 200x200um area
fracture: JBXFILER, 1nm grid

**Develop:** 2min n-Amyl Acetate, IPA rinse
develop temperature: 21C